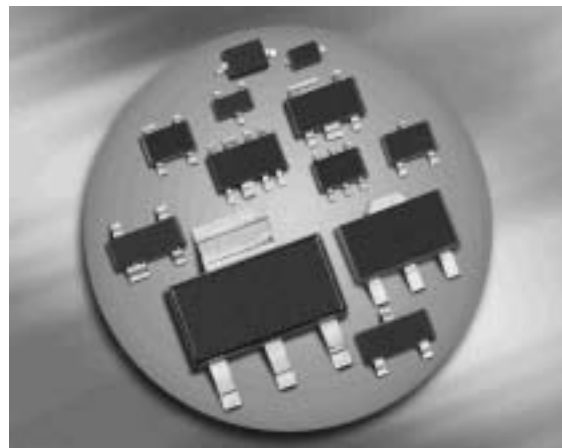


**NPN Silicon AF Transistors**

- For AF input stages and driver applications
- High current gain
- Low collector-emitter saturation voltage
- Low noise between 30 Hz and 15 kHz
- Complementary types:  
BC856...-BC860...(PNP)
- Pb-free (RoHS compliant) package <sup>1)</sup>
- Qualified according AEC Q101



<sup>1</sup>Pb-containing package may be available upon special request

| Type     | Marking | Pin Configuration |     |     |   |   |   | Package  |
|----------|---------|-------------------|-----|-----|---|---|---|----------|
|          |         | 1=B               | 2=E | 3=C | - | - | - |          |
| BC846A   | 1As     | 1=B               | 2=E | 3=C | - | - | - | SOT23    |
| BC846B   | 1Bs     | 1=B               | 2=E | 3=C | - | - | - | SOT23    |
| BC846BW  | 1Bs     | 1=B               | 2=E | 3=C | - | - | - | SOT323   |
| BC847A   | 1Es     | 1=B               | 2=E | 3=C | - | - | - | SOT23    |
| BC847B   | 1Fs     | 1=B               | 2=E | 3=C | - | - | - | SOT23    |
| BC847BF  | 1Fs     | 1=B               | 2=E | 3=C | - | - | - | TSFP-3   |
| BC847BL3 | 1F      | 1=B               | 2=E | 3=C | - | - | - | TSLP-3-1 |
| BC847BT  | 1F      | 1=B               | 2=E | 3=C | - | - | - | SC75     |
| BC847BW  | 1Fs     | 1=B               | 2=E | 3=C | - | - | - | SOT323   |
| BC847C   | 1Gs     | 1=B               | 2=E | 3=C | - | - | - | SOT23    |
| BC847CW  | 1Gs     | 1=B               | 2=E | 3=C | - | - | - | SOT323   |
| BC848A   | 1Js     | 1=B               | 2=E | 3=C | - | - | - | SOT23    |
| BC848AW  | 1Js     | 1=B               | 2=E | 3=C | - | - | - | SOT323   |
| BC848B   | 1Ks     | 1=B               | 2=E | 3=C | - | - | - | SOT23    |
| BC848BF  | 1Ks     | 1=B               | 2=E | 3=C | - | - | - | TSFP-3   |
| BC848BL3 | 1K      | 1=B               | 2=E | 3=C | - | - | - | TSLP-3-1 |
| BC848BW  | 1Ks     | 1=B               | 2=E | 3=C | - | - | - | SOT323   |
| BC848C   | 1Ls     | 1=B               | 2=E | 3=C | - | - | - | SOT23    |
| BC848CW  | 1Ls     | 1=B               | 2=E | 3=C | - | - | - | SOT323   |
| BC849B   | 2Bs     | 1=B               | 2=E | 3=C | - | - | - | SOT23    |
| BC849BF  | 2Bs     | 1=B               | 2=E | 3=C | - | - | - | TSFP-3   |
| BC849C   | 2Cs     | 1=B               | 2=E | 3=C | - | - | - | SOT23    |
| BC849CW  | 2Cs     | 1=B               | 2=E | 3=C | - | - | - | SOT323   |
| BC850B   | 2Fs     | 1=B               | 2=E | 3=C | - | - | - | SOT23    |
| BF850BF  | 2Fs     | 1=B               | 2=E | 3=C | - | - | - | TSFP-3   |
| BC850BW  | 2Fs     | 1=B               | 2=E | 3=C | - | - | - | SOT323   |
| BC850C   | 2Gs     | 1=B               | 2=E | 3=C | - | - | - | SOT23    |
| BC850CW  | 2Gs     | 1=B               | 2=E | 3=C | - | - | - | SOT323   |

**Maximum Ratings**

| Parameter  | Symbol    | Value                           | Unit |
|--|-----------|---------------------------------|------|
| Collector-emitter voltage<br>BC846...<br>BC847..., BC850...<br>BC848..., BC849...  | $V_{CEO}$ | 65<br>45<br>30                  | V    |
| Collector-emitter voltage<br>BC846...<br>BC847..., BC850...<br>BC848..., BC849...  | $V_{CES}$ | 80<br>50<br>30                  |      |
| Collector-base voltage<br>BC846...<br>BC847..., BC850...<br>BC848..., BC849...   | $V_{CBO}$ | 80<br>50<br>30                  |      |
| Emitter-base voltage<br>BC846...<br>BC847..., BC850...<br>BC848..., BC849...   | $V_{EBO}$ | 6<br>6<br>6                     |      |
| Collector current  | $I_C$     | 100                             | mA   |
| Peak collector current   | $I_{CM}$  | 200                             |      |
| Total power dissipation-<br>$T_S \leq 71\text{ °C}$ , BC846-BC850<br>$T_S \leq 128\text{ °C}$ , BC847F-BC850F<br>$T_S \leq 135\text{ °C}$ , BC847L3-BC848L3<br>$T_S \leq 109\text{ °C}$ , BC847T<br>$T_S \leq 124\text{ °C}$ , BC846W-BC850W | $P_{tot}$ | 330<br>250<br>250<br>250<br>250 | mW   |
| Junction temperature   | $T_j$     | 150                             | °C   |
| Storage temperature  | $T_{stg}$ | -65 ... 150                     |      |

**Thermal Resistance**

| Parameter                                | Symbol     | Value      | Unit |
|--|------------|------------|------|
| Junction - soldering point <sup>1)</sup> | $R_{thJS}$ |            | K/W  |
| BC846-BC850                              |            | $\leq 240$ |      |
| BC847F-BC850F                            |            | $\leq 90$  |      |
| BC847L3-BC848L3                          |            | $\leq 60$  |      |
| BC847T                                   |            | $\leq 165$ |      |
| BC846W-BC850W                            |            | $\leq 105$ |      |

<sup>1)</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

| Parameter   | Symbol        | Values                           |  |                                  | Unit          |
|---|---------------|----------------------------------|--|----------------------------------|---------------|
|   |               | min.                             | typ.                                   | max.                             |               |
| <b>DC Characteristics</b>   |               |                                  |  |                                  |               |
| Collector-emitter breakdown voltage<br>$I_C = 10\text{ mA}$ , $I_B = 0$ , BC846...<br>$I_C = 10\text{ mA}$ , $I_B = 0$ , BC847..., BC850...<br>$I_C = 10\text{ mA}$ , $I_B = 0$ , BC848..., BC849...  | $V_{(BR)CEO}$ | 65<br>45<br>30                   | -<br>-<br>-                            | -<br>-<br>-                      | V             |
| Collector-base breakdown voltage<br>$I_C = 10\text{ }\mu\text{A}$ , $I_E = 0$ , BC846...<br>$I_C = 10\text{ }\mu\text{A}$ , $I_E = 0$ , BC847..., BC850...<br>$I_C = 10\text{ }\mu\text{A}$ , $I_E = 0$ , BC848..., BC849...  | $V_{(BR)CBO}$ | 80<br>50<br>30                   | -<br>-<br>-                            | -<br>-<br>-                      |               |
| Emitter-base breakdown voltage<br>$I_E = 0$ , $I_C = 10\text{ }\mu\text{A}$   | $V_{(BR)EBO}$ | -                                | 6                                      | -                                |               |
| Collector-base cutoff current<br>$V_{CB} = 45\text{ V}$ , $I_E = 0$<br>$V_{CB} = 30\text{ V}$ , $I_E = 0$ , $T_A = 150\text{ }^\circ\text{C}$   | $I_{CBO}$     | -<br>-                           | 0.015<br>5                             | -<br>-                           | $\mu\text{A}$ |
| DC current gain <sup>1)</sup><br>$I_C = 10\text{ }\mu\text{A}$ , $V_{CE} = 5\text{ V}$ , $h_{FE}$ -grp.A<br>$I_C = 10\text{ }\mu\text{A}$ , $V_{CE} = 5\text{ V}$ , $h_{FE}$ -grp.B<br>$I_C = 10\text{ }\mu\text{A}$ , $V_{CE} = 5\text{ V}$ , $h_{FE}$ -grp.C<br>$I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $h_{FE}$ -grp.A<br>$I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $h_{FE}$ -grp.B<br>$I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $h_{FE}$ -grp.C | $h_{FE}$      | -<br>-<br>-<br>110<br>200<br>420 | 140<br>250<br>480<br>180<br>290<br>520 | -<br>-<br>-<br>220<br>450<br>800 | -             |
| Collector-emitter saturation voltage <sup>1)</sup><br>$I_C = 10\text{ mA}$ , $I_B = 0.5\text{ mA}$<br>$I_C = 100\text{ mA}$ , $I_B = 5\text{ mA}$   | $V_{CEsat}$   | -<br>-                           | 90<br>200                              | 250<br>600                       | mV            |
| Base emitter saturation voltage <sup>1)</sup><br>$I_C = 10\text{ mA}$ , $I_B = 0.5\text{ mA}$<br>$I_C = 100\text{ mA}$ , $I_B = 5\text{ mA}$  | $V_{BEsat}$   | -<br>-                           | 700<br>900                             | -<br>-                           |               |
| Base-emitter voltage <sup>1)</sup><br>$I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$<br>$I_C = 10\text{ mA}$ , $V_{CE} = 5\text{ V}$   | $V_{BE(ON)}$  | 580<br>-                         | 660<br>-                               | 700<br>770                       |               |

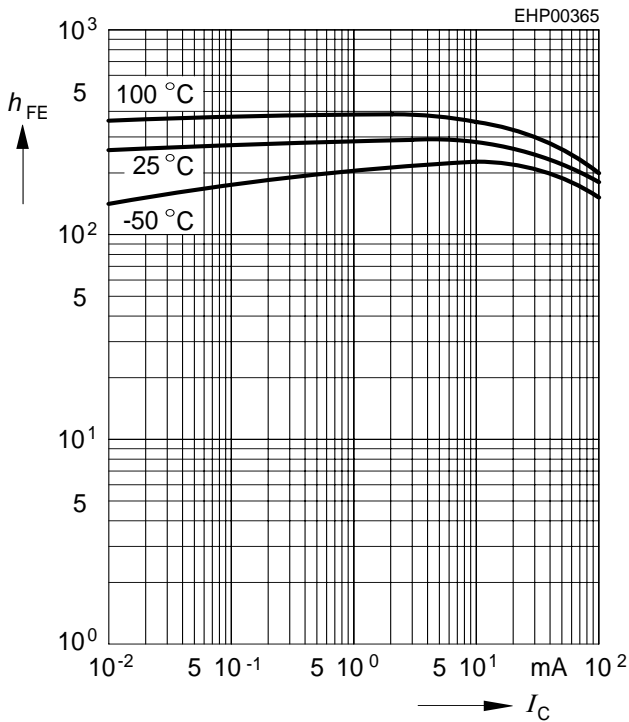
<sup>1)</sup>Pulse test:  $t < 300\mu\text{s}$ ;  $D < 2\%$

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

| Parameter   | Symbol    | Values |                   |       | Unit          |           |
|---|-----------|--------|-------------------|-------|---------------|-----------|
|   |           | min.   | typ.              | max.  |               |           |
| <b>AC Characteristics</b>   |           |        |                   |       |               |           |
| Transition frequency<br>$I_C = 10\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $f = 100\text{ MHz}$   | $f_T$     | -      | 250               | -     | MHz           |           |
| Collector-base capacitance<br>$V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$   | $C_{cb}$  | -      | 0.95              | -     | pF            |           |
| Emitter-base capacitance<br>$V_{EB} = 0.5\text{ V}$ , $f = 1\text{ MHz}$  | $C_{eb}$  | -      | 9                 | -     |               |           |
| Short-circuit input impedance<br>$I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $f = 1\text{ kHz}$ , $h_{FE}$ -grp.A<br>$I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $f = 1\text{ kHz}$ , $h_{FE}$ -grp.B<br>$I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $f = 1\text{ kHz}$ , $h_{FE}$ -grp.C               | $h_{11e}$ | -      | 2.7<br>4.5<br>8.7 | -     | k $\Omega$    |           |
| Open-circuit reverse voltage transf. ratio<br>$I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $f = 1\text{ kHz}$ , $h_{FE}$ -grp.A<br>$I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $f = 1\text{ kHz}$ , $h_{FE}$ -grp.B<br>$I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $f = 1\text{ kHz}$ , $h_{FE}$ -grp.C  | $h_{12e}$ | -      | 1.5<br>2<br>3     | -     |               | $10^{-4}$ |
| Short-circuit forward current transf. ratio<br>$I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $f = 1\text{ kHz}$ , $h_{FE}$ -grp.A<br>$I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $f = 1\text{ kHz}$ , $h_{FE}$ -grp.B<br>$I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $f = 1\text{ kHz}$ , $h_{FE}$ -grp.C | $h_{21e}$ | -      | 200<br>330<br>600 | -     |               |           |
| Open-circuit output admittance<br>$I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $f = 1\text{ kHz}$ , $h_{FE}$ -grp.A<br>$I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $f = 1\text{ kHz}$ , $h_{FE}$ -grp.B<br>$I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $f = 1\text{ kHz}$ , $h_{FE}$ -grp.C              | $h_{22e}$ | -      | 18<br>30<br>60    | -     | $\mu\text{S}$ |           |
| Noise figure<br>$I_C = 200\text{ }\mu\text{A}$ , $V_{CE} = 5\text{ V}$ , $f = 1\text{ kHz}$ ,<br>$\Delta f = 200\text{ Hz}$ , $R_S = 2\text{ k}\Omega$ , BC849..., BC850...   | $F$       | -      | 1.2               | 4     | dB            |           |
| Equivalent noise voltage<br>$I_C = 200\text{ }\mu\text{A}$ , $V_{CE} = 5\text{ V}$ , $R_S = 2\text{ k}\Omega$ ,<br>$f = 10 \dots 50\text{ Hz}$ , BC850...   | $V_n$     | -      | -                 | 0.135 | $\mu\text{V}$ |           |

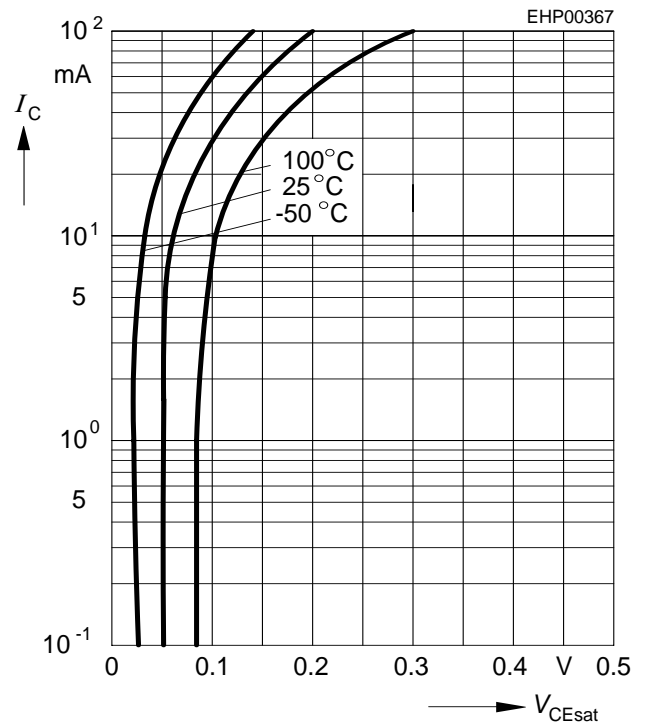
**DC current gain  $h_{FE} = f(I_C)$**

$V_{CE} = 5\text{ V}$



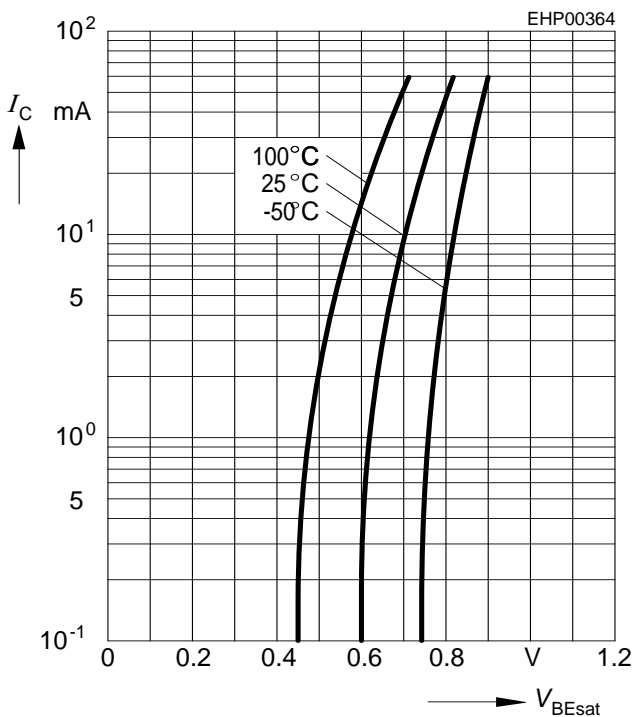
**Collector-emitter saturation voltage**

$I_C = f(V_{CEsat}), h_{FE} = 20$



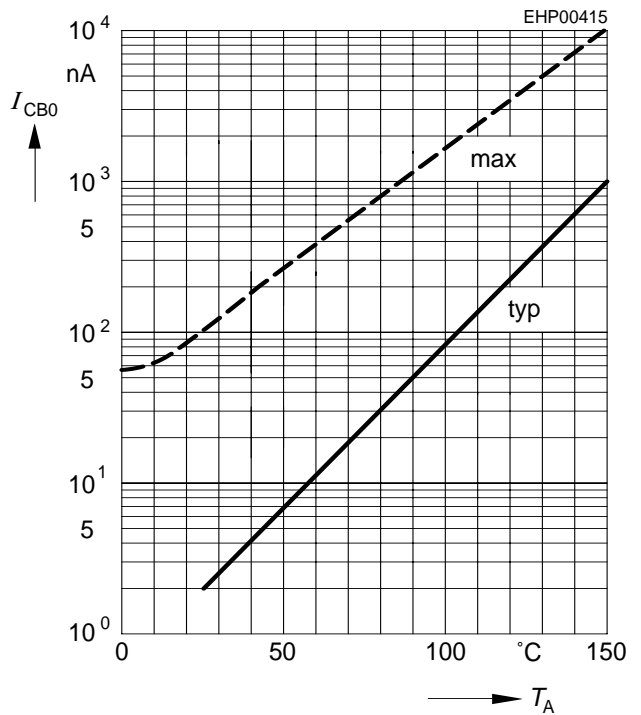
**Base-emitter saturation voltage**

$I_C = f(V_{BEsat}), h_{FE} = 20$



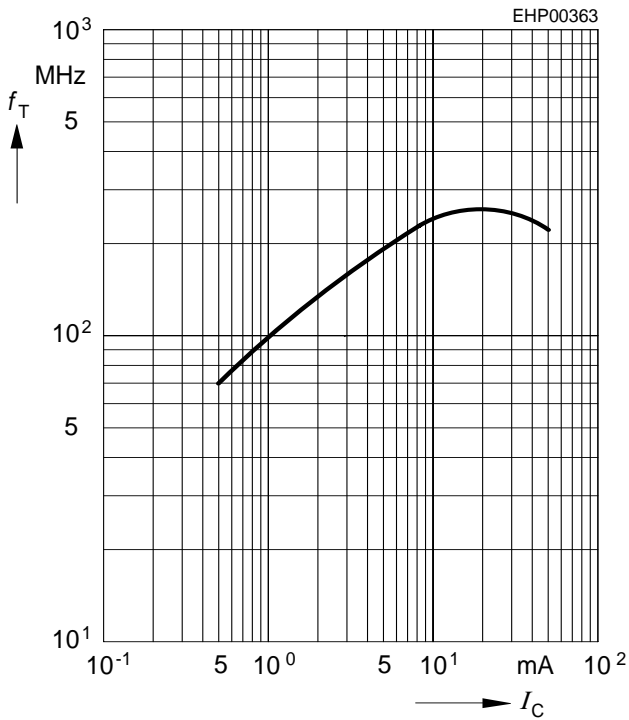
**Collector cutoff current  $I_{CBO} = f(T_A)$**

$V_{CB} = 30\text{ V}$



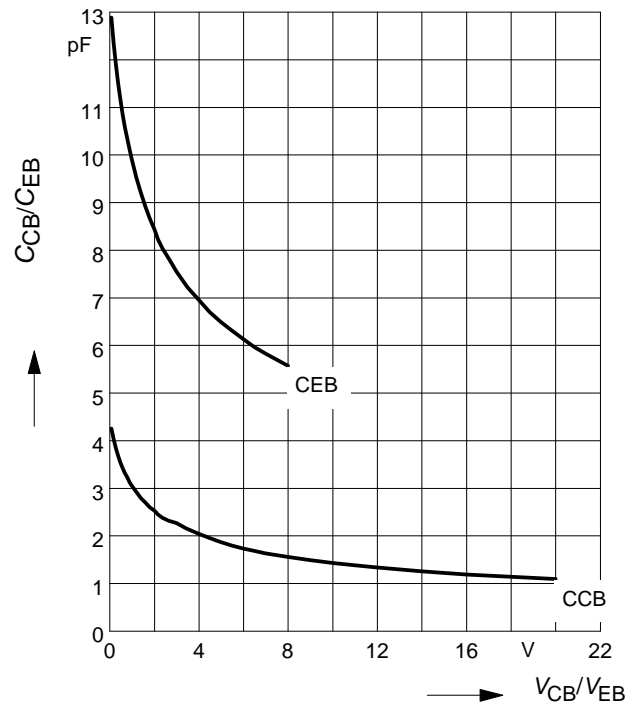
Transition frequency  $f_T = f(I_C)$

$V_{CE} = 5\text{ V}$



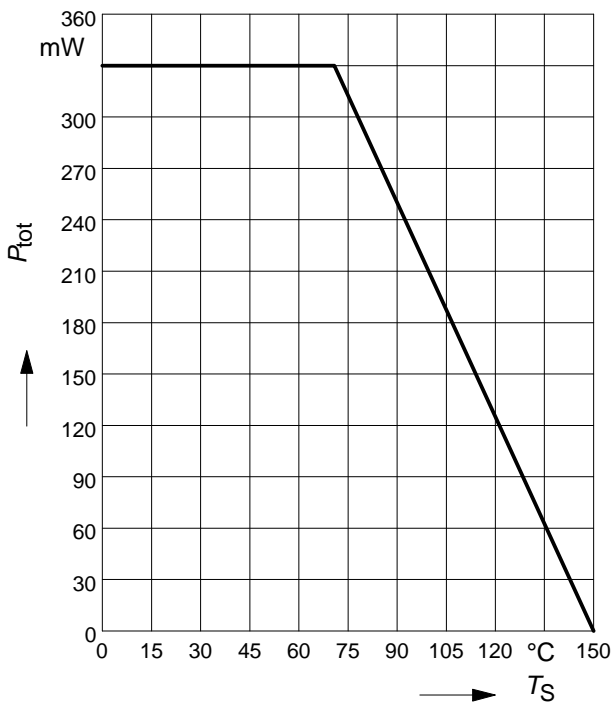
Collector-base capacitance  $C_{cb} = f(V_{CB})$

Emitter-base capacitance  $C_{eb} = f(V_{EB})$



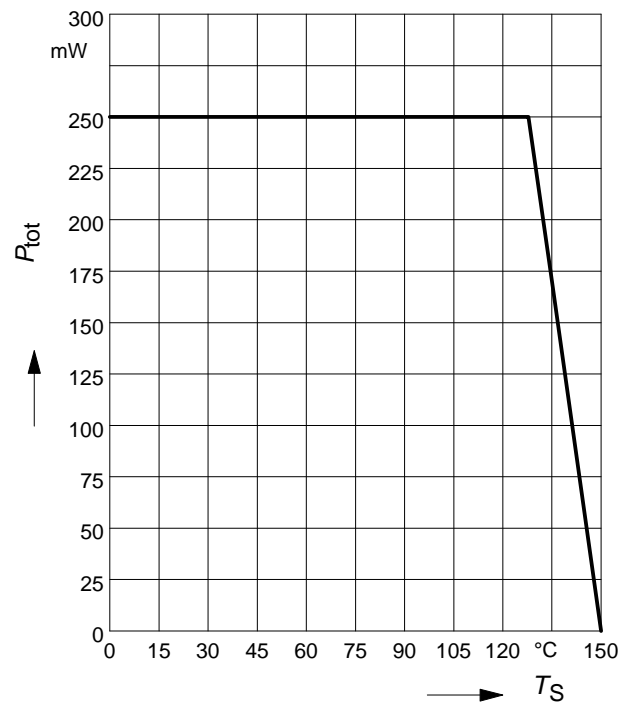
Total power dissipation  $P_{tot} = f(T_S)$

BC846-BC850



Total power dissipation  $P_{tot} = f(T_S)$

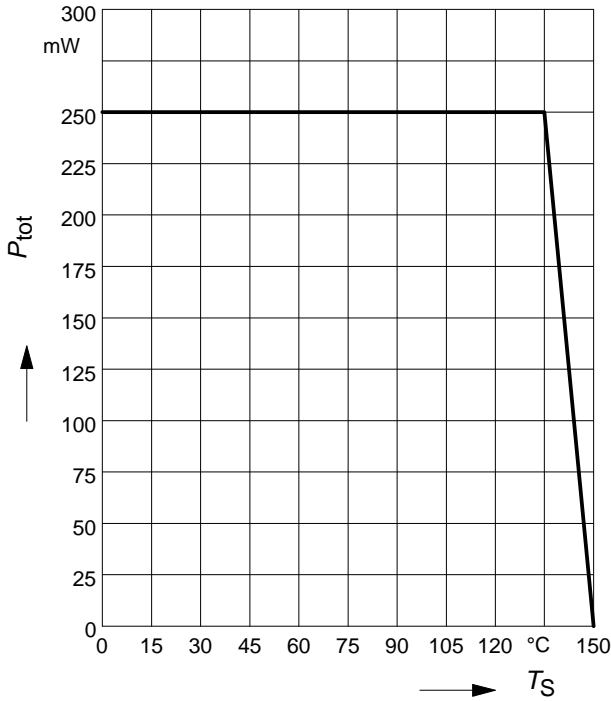
BC847BF-BC850BF





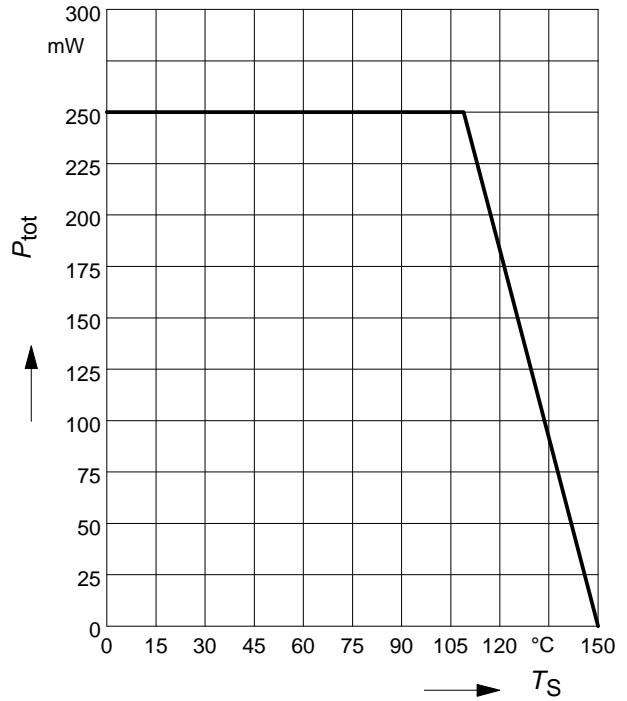
**Total power dissipation  $P_{tot} = f(T_S)$**

BC847BL3/BC848BL3



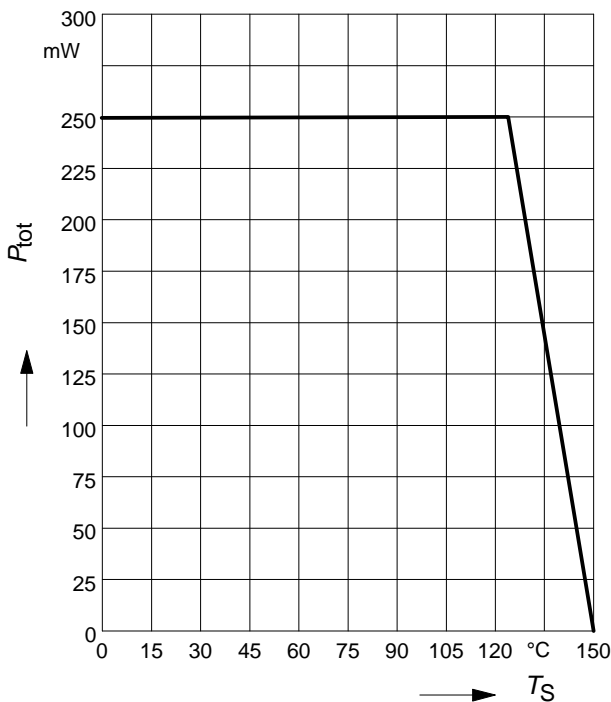
**Total power dissipation  $P_{tot} = f(T_S)$**

BC847BT



**Total power dissipation  $P_{tot} = f(T_S)$**

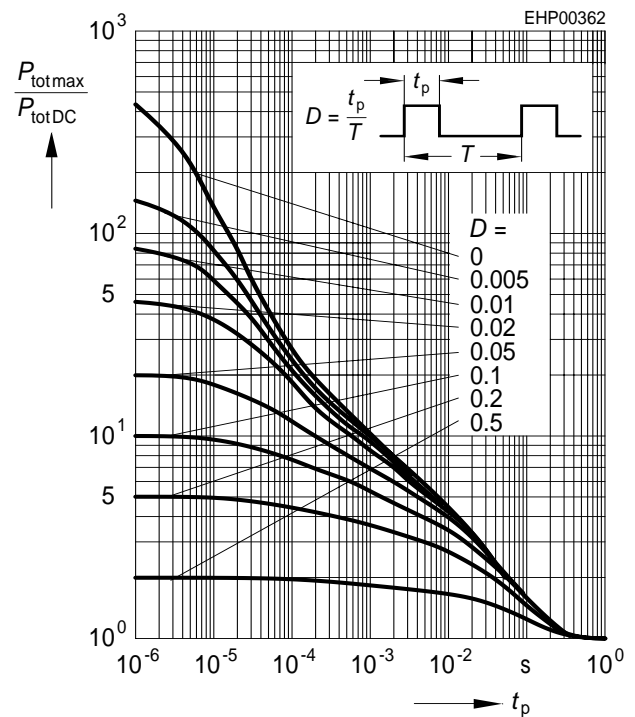
BC846W-BC850W



**Permissible Pulse Load**

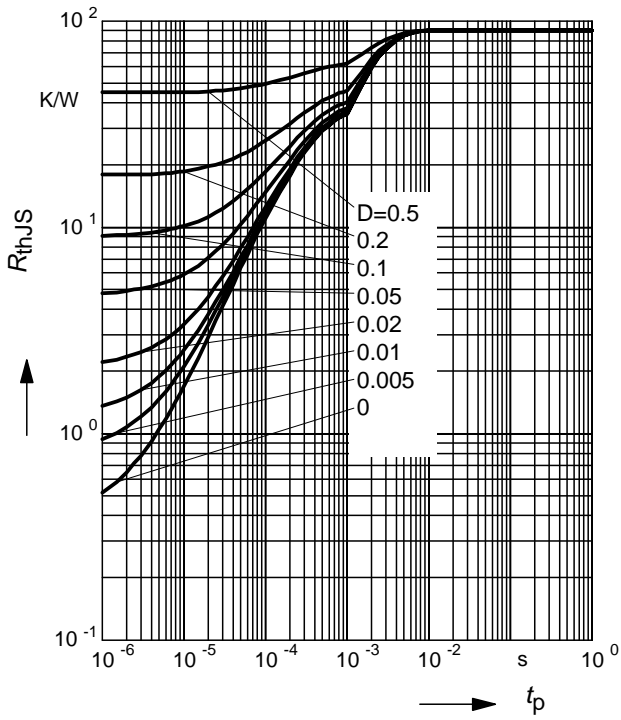
$P_{totmax}/P_{totDC} = f(t_p)$

BC846/W-BC850/W



**Permissible Puls Load  $R_{thJS} = f(t_p)$**

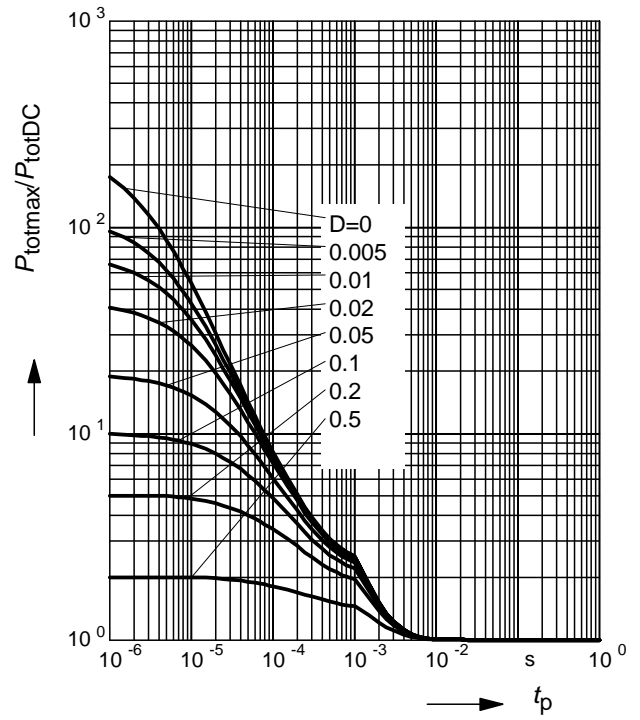
BC847BF-BC850BF



**Permissible Pulse Load**

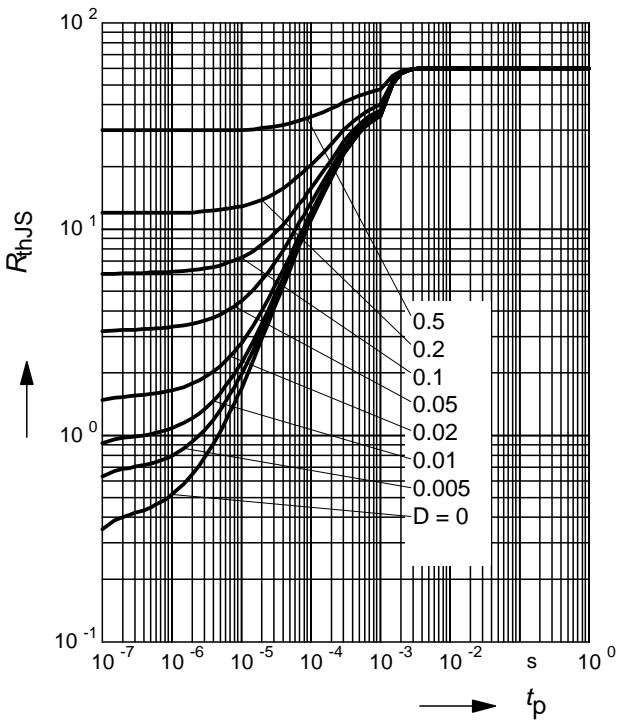
$P_{totmax}/P_{totDC} = f(t_p)$

BC847BF-BC850BF



**Permissible Puls Load  $R_{thJS} = f(t_p)$**

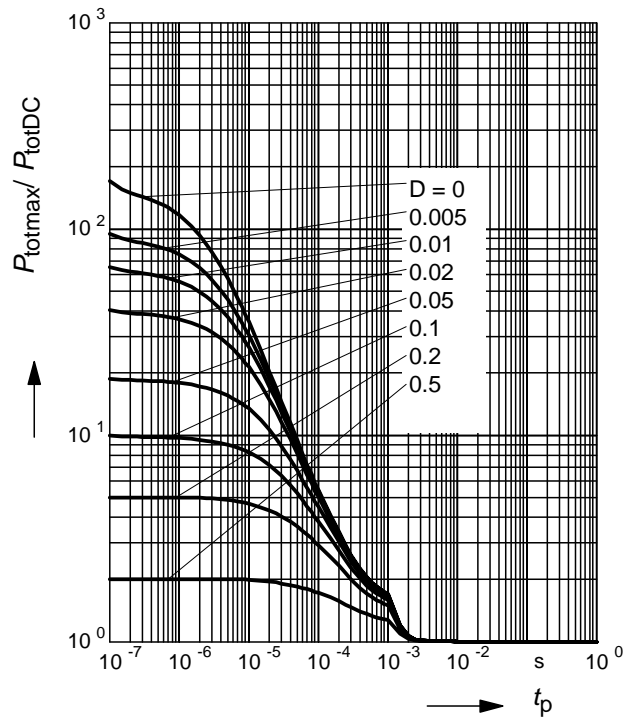
BC847BL3, BC848BL3



**Permissible Pulse Load**

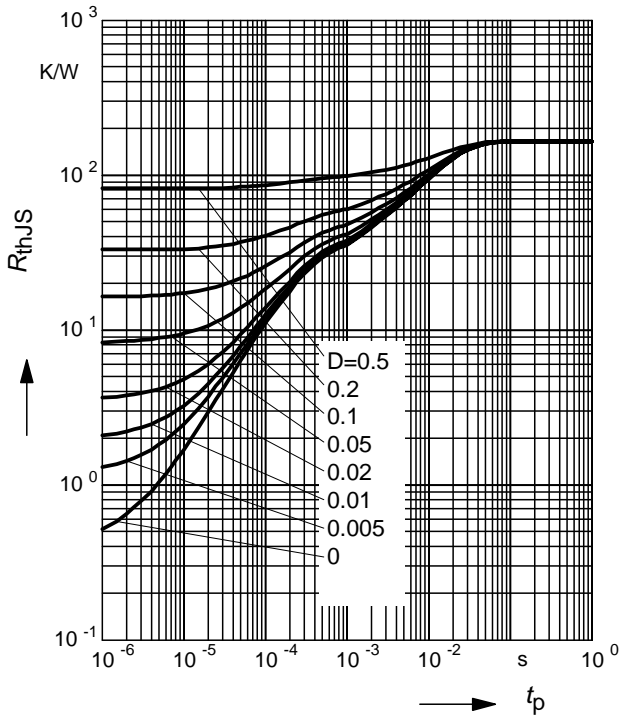
$P_{totmax}/P_{totDC} = f(t_p)$

BC847BL3, BC848BL3



**Permissible Puls Load  $R_{thJS} = f(t_p)$**

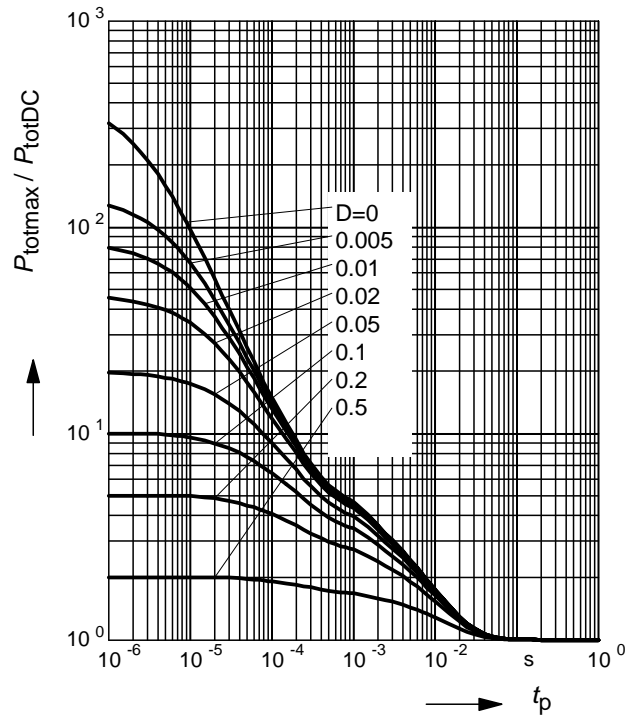
BC847BT



**Permissible Pulse Load**

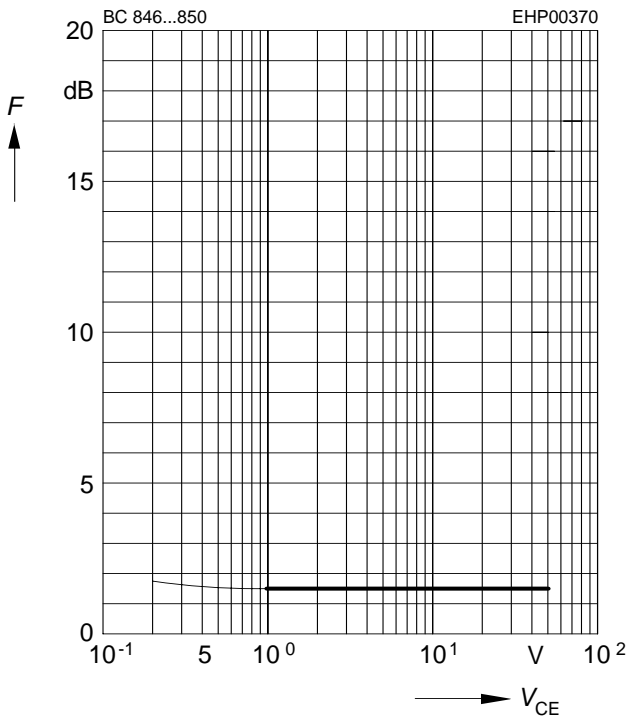
$P_{totmax}/P_{totDC} = f(t_p)$

BC847BT



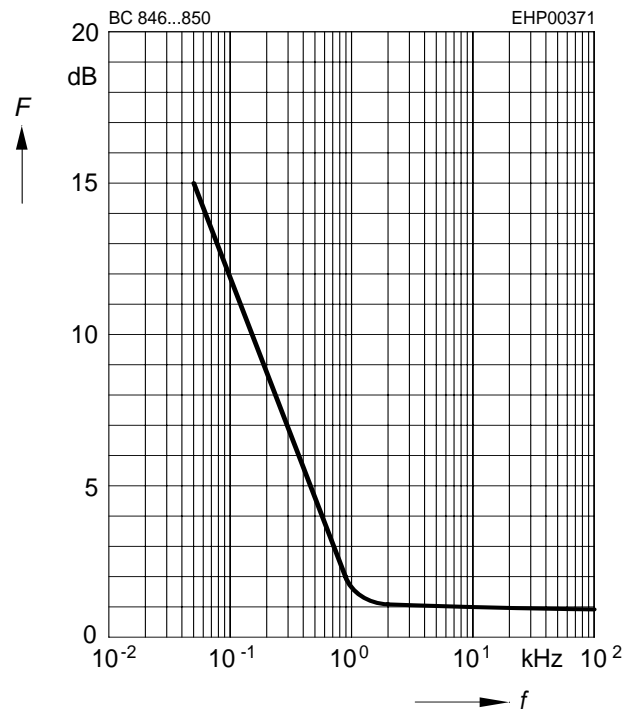
**Noise figure  $F = f(V_{CE})$**

$I_C = 0.2mA, R_S = 2k\Omega, f = 1kHz$



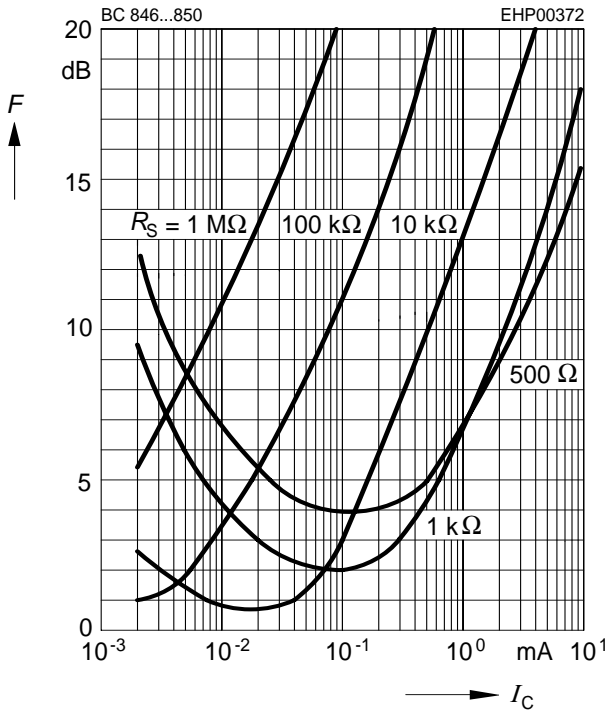
**Noise figure  $F = f(f)$**

$I_C = 0.2 mA, V_{CE} = 5V, R_S = 2 k\Omega$



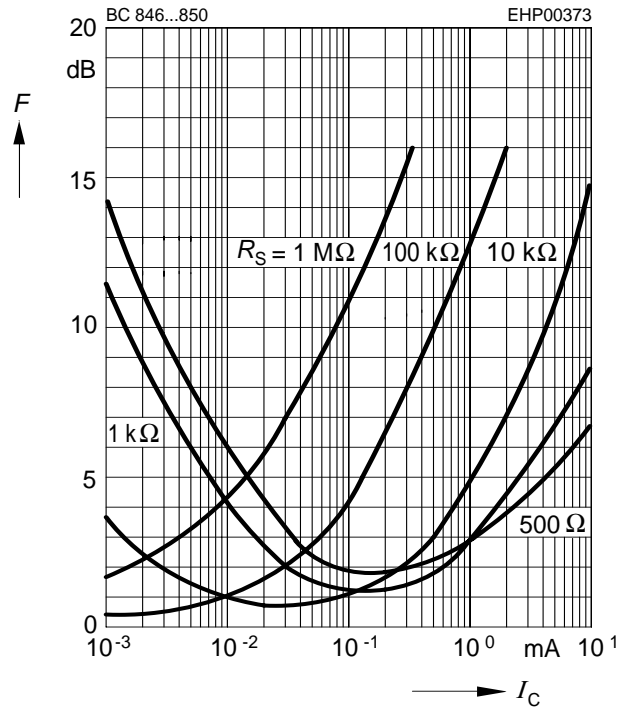
Noise figure  $F = f(I_C)$

$V_{CE} = 5V, f = 120Hz$



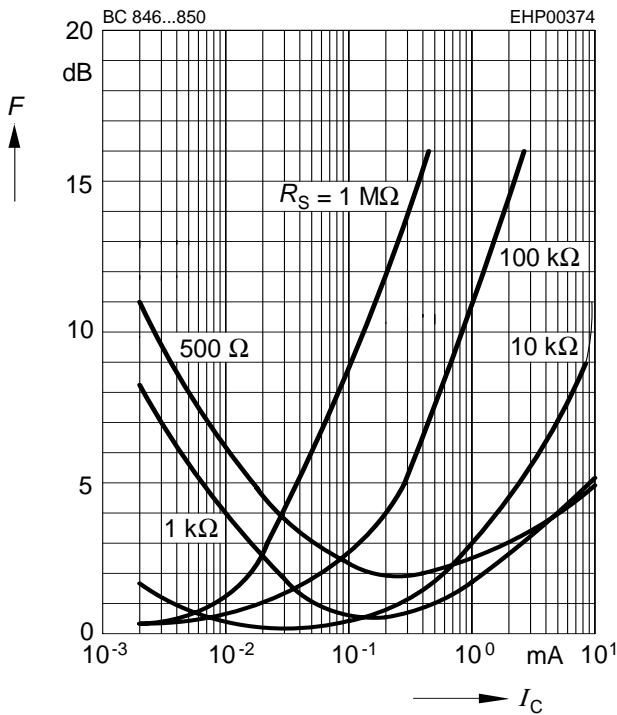
Noise figure  $F = f(I_C)$

$V_{CE} = 5V, f = 1kHz$

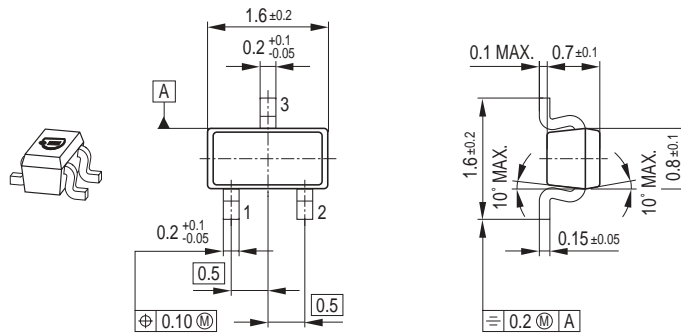


Noise figure  $F = f(I_C)$

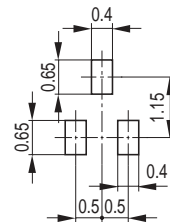
$V_{CE} = 5V, f = 10kHz$



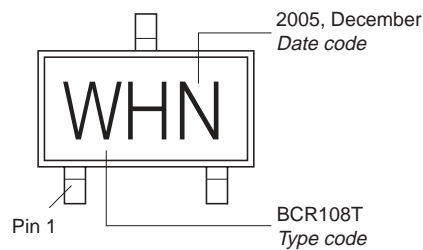
Package Outline



Foot Print

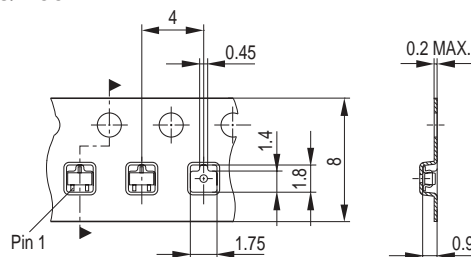


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel  
 Reel ø330 mm = 10.000 Pieces/Reel



Date Code marking for discrete packages with one digit (SCD80, SC79, SC75<sup>1)</sup>) CES-Code

| Month | 2003 | 2004 | 2005 | 2006 | 2007 | 2008 | 2009 | 2010 | 2011 | 2012 | 2013 | 2014 |
|-------|------|------|------|------|------|------|------|------|------|------|------|------|
| 01    | a    | p    | A    | P    | a    | p    | A    | P    | a    | p    | A    | P    |
| 02    | b    | q    | B    | Q    | b    | q    | B    | Q    | b    | q    | B    | Q    |
| 03    | c    | r    | C    | R    | c    | r    | C    | R    | c    | r    | C    | R    |
| 04    | d    | s    | D    | S    | d    | s    | D    | S    | d    | s    | D    | S    |
| 05    | e    | t    | E    | T    | e    | t    | E    | T    | e    | t    | E    | T    |
| 06    | f    | u    | F    | U    | f    | u    | F    | U    | f    | u    | F    | U    |
| 07    | g    | v    | G    | V    | g    | v    | G    | V    | g    | v    | G    | V    |
| 08    | h    | x    | H    | X    | h    | x    | H    | X    | h    | x    | H    | X    |
| 09    | j    | y    | J    | Y    | j    | y    | J    | Y    | j    | y    | J    | Y    |
| 10    | k    | z    | K    | Z    | k    | z    | K    | Z    | k    | z    | K    | Z    |
| 11    | l    | 2    | L    | 4    | l    | 2    | L    | 4    | l    | 2    | L    | 4    |
| 12    | n    | 3    | N    | 5    | n    | 3    | N    | 5    | n    | 3    | N    | 5    |

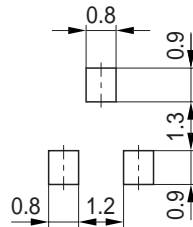
1) New Marking Layout for SC75, implemented at October 2005.

Package Outline

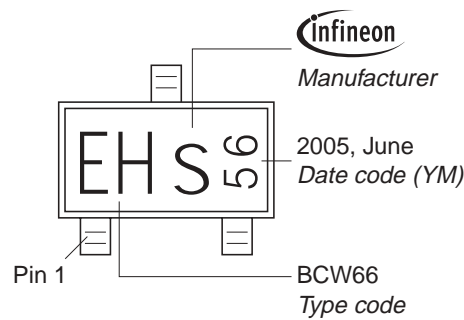


1) Lead width can be 0.6 max. in dambar area

Foot Print

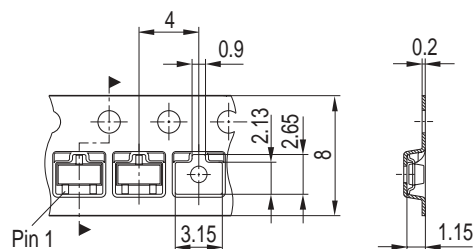


Marking Layout (Example)

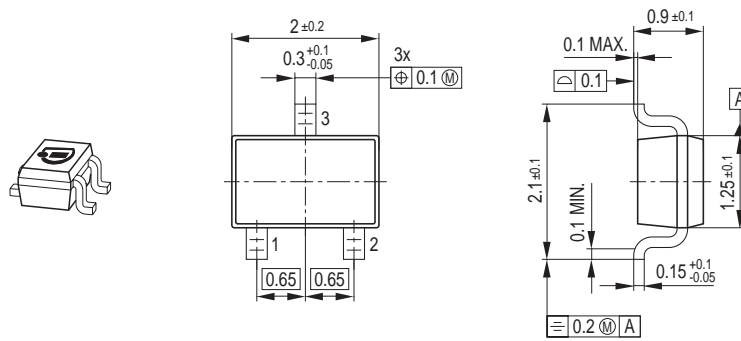


Standard Packing

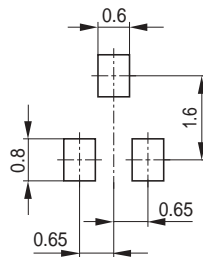
Reel  $\varnothing$ 180 mm = 3.000 Pieces/Reel  
 Reel  $\varnothing$ 330 mm = 10.000 Pieces/Reel



Package Outline



Foot Print

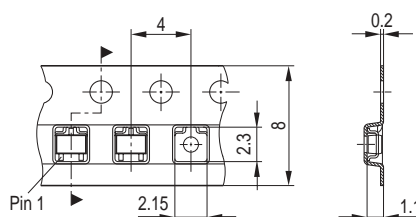


Marking Layout (Example)



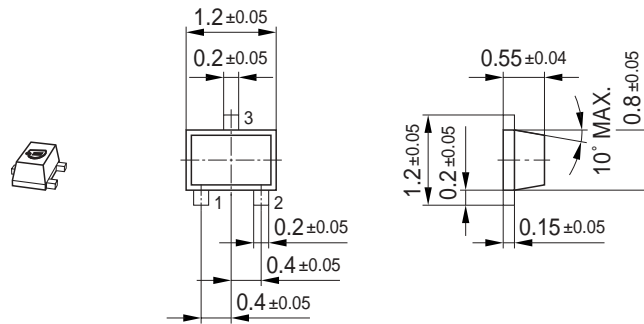
Standard Packing

Reel  $\varnothing$ 180 mm = 3.000 Pieces/Reel  
 Reel  $\varnothing$ 330 mm = 10.000 Pieces/Reel

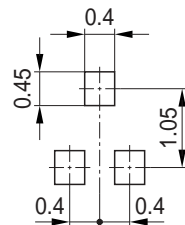




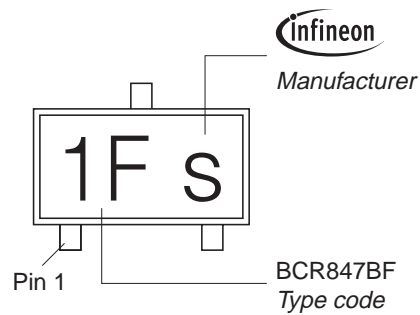
Package Outline



Foot Print

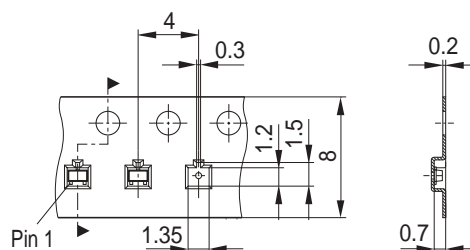


Marking Layout (Example)

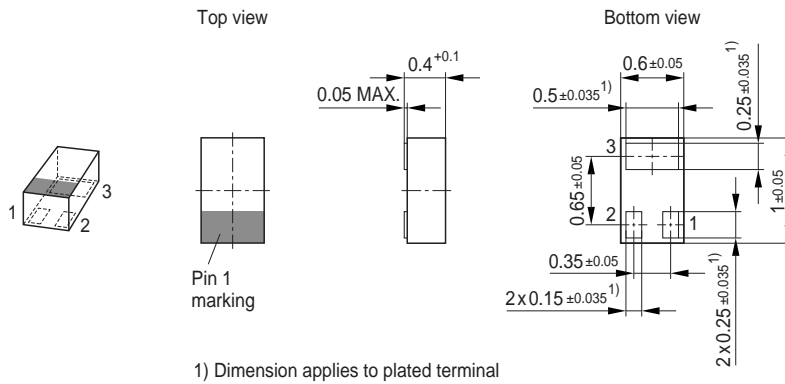


Standard Packing

Reel  $\varnothing$ 180 mm = 3.000 Pieces/Reel  
 Reel  $\varnothing$ 330 mm = 10.000 Pieces/Reel

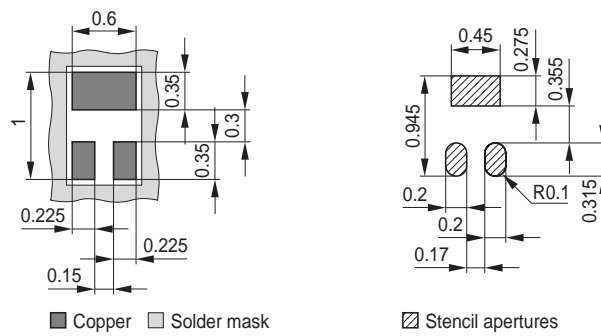


### Package Outline

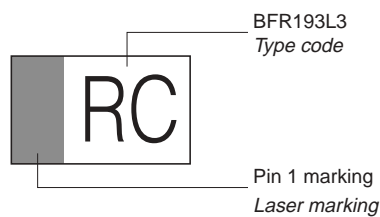


### Foot Print

For board assembly information please refer to Infineon website "Packages"

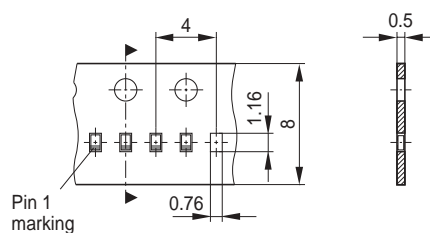


### Marking Layout (Example)



### Standard Packing

Reel  $\varnothing$ 180 mm = 15.000 Pieces/Reel



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### Наши контакты:

**Телефон:** +7 812 627 14 35

**Электронная почта:** [sales@st-electron.ru](mailto:sales@st-electron.ru)

**Адрес:** 198099, Санкт-Петербург,  
Промышленная ул, дом № 19, литера Н,  
помещение 100-Н Офис 331